

**What is claimed is:**

1. A method of manufacturing an array substrate, comprising:  
forming an electrode line on a substrate using a wet etching technique; and  
forming an organic insulating layer on an exposed surface of the substrate  
while covering the electrode line,  
wherein the electrode line has a side portion having an overhang or a taper  
angle of more than 45°C.
2. The method of claim 1, wherein the organic insulating layer is made of one  
of benzocyclobutene, an olefin-based insulating material, an acrylic-based insulating  
material, and a silicon-based insulating material.
3. The method of claim 1, wherein the electrode line has first and second metal  
layers of a dual-layered structure, and a side portion of the first metal layer is over  
etched than that of the second metal layer.
4. The method of claim 3, wherein the first metal layer is made of one of  
aluminum, an aluminum alloy, AlNd, copper and a copper alloy.
5. The method of claim 3, wherein the second metal layer is made of one of Cr,  
Cr-alloy, Mo, Mo-alloy, Ta, Ta-alloy, W, and W-alloy.
6. The method of claim 1, wherein the electrode line has first, second and third  
metal layers of a three-layered structure, and a side portion of the second metal layer is

over etched than that of the first and third metal layers.

7. An array substrate for a liquid crystal display device, comprising:

an electrode line formed on a substrate; and

an organic insulating layer formed on an exposed surface of the substrate while covering the electrode line,

wherein the electrode line has an overhang or a taper angle of a side portion of the electrode is more than 45°C.

8. The array substrate of claim 7, wherein the organic insulating layer is made of one of benzocyclobutene, an olefin-based insulating material, an acrylic-based insulating material, and a silicon-based insulating material.

9. The array substrate of claim 7, wherein the electrode line has first and second metal layers of a dual-layered structure, and a side portion of the first metal layer is over etched than that of the second metal layer.

10. The array substrate of claim 9, wherein the first metal layer is made of one of aluminum, an aluminum alloy, AlNd, copper and a copper alloy.

11. The array substrate of claim 9, wherein the second metal layer is made of one of Cr, Cr-alloy, Mo, Mo-alloy, Ta, Ta-alloy, W, and W-alloy.

12. The array substrate of claim 11, wherein the electrode line has first, second and third metal layers of a three-layered structure, and a side portion of the second metal layer is over etched than that of the first and third metal layers.